

logical state of the art and enhance the possibility of realizing space-based optical communication systems.

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Erratum

Our sincere apologies to Paul F. Sass for the inadvertent error made in his article "Why Is the Army Interested in Spread Spectrum?" which appeared in the July *IEEE Communications Magazine*. The error, one line repeated twice and one line therefore omitted, appeared in the third paragraph of the first page of the article, p. 23. The corrected paragraph is printed below.

The Army's communications systems today [3] are turning to spread spectrum for the same reasons. Our next generation combat net radio, Single Channel Ground and Airborne Radio Subsystem (SINCGARS), was designed from the

ground up to provide protection against jamming in the tactical VHF band (30-88 MHz). Our Position Location and Reporting System (PLRS), the first of a new generation of tactical radio data networks, was intended to provide a tactical position location system capable of withstanding EW attacks while simultaneously distributing the needed position location information in ground environments. The Joint Tactical Information Distribution System (JTIDS) was driven from its inception by DoD's need for a high-AJ secure data distribution system. Spread spectrum provided a technique to satisfy all of these objectives as far back as the early 1970's.